

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 07-086269

(43)Date of publication of application : 31.03.1995

(51)Int.Cl.

H01L 21/314

H01L 29/786

(21)Application number : 05-226178

(71)Applicant : FUJITSU LTD

(22)Date of filing : 10.09.1993

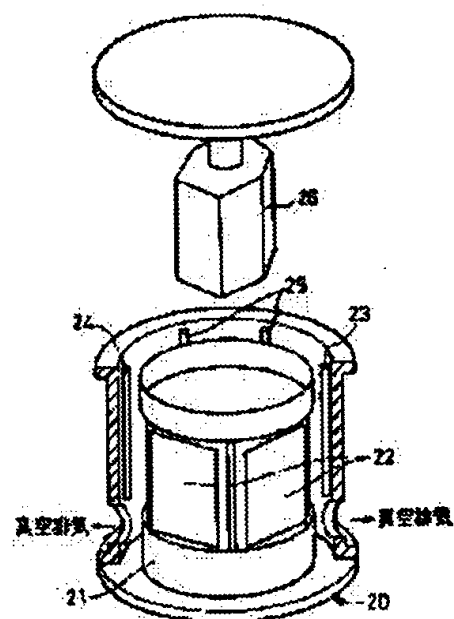
(72)Inventor : KOSUGI KIYOHISA
WATABE JUNICHI
IGARASHI MAKOTO
SHIROKI IKUO

(54) ALUMINA FILM FORMATION AND MANUFACTURE OF THIN FILM TRANSISTOR USING SAME

(57)Abstract:

PURPOSE: To form an alumina film which contains less particles by using oxide organic material as oxidizing material gas in forming an alumina film on a substrate by alternately exposing the substrate to organic metal gas which contains aluminum and oxidizing material gas.

CONSTITUTION: In case of forming an alumina film on a substrate 22 by alternately exposing the substrate 22 to organic metal gas, which contains aluminum, and oxidizing material gas, oxide organic material is used as the oxidizing material gas. For example, the substrate 22 is loaded on the external plane of a rotating body 21 using the ALD(atomic layer deposition) film forming device shown in the figure, and the substrate 22 is heated to a desired temperature by a heater 26 arranged in the rotating body 21. Trimethylaluminum, ethylene oxide and argon gas are supplied from nozzles 23-25, and an alumina film is formed by rotating the rotating body 21 under the low pressure of 2×10^{-5} Torr at 450° C.



LEGAL STATUS

- [Date of request for examination]
- [Date of sending the examiner's decision of rejection]
- [Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]
- [Date of final disposal for application]
- [Patent number]
- [Date of registration]
- [Number of appeal against examiner's decision of rejection]
- [Date of requesting appeal against examiner's decision of rejection]
- [Date of extinction of right]